

FDG314P

Digital FET, P-Channel

General Description

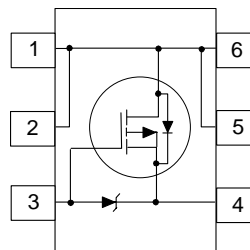
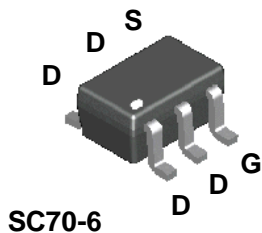
This P-Channel enhancement mode field effect transistor is produced using Fairchild Semiconductor's proprietary, high cell density, DMOS technology. This very high density process is tailored to minimize on-state resistance at low gate drive conditions. This device is designed especially for battery power applications such as notebook computers and cellular phones. This device has excellent on-state resistance even at gate drive voltages as low as 2.5 volts.

Applications

- Power Management
- Load switch
- Signal switch

Features

- -0.65 A, -25 V. $R_{DS(ON)} = 1.1 \Omega @ V_{GS} = -4.5 V$
 $R_{DS(ON)} = 1.5 \Omega @ V_{GS} = -2.7 V.$
- Very low gate drive requirements allowing direct operation in 3V circuits ($V_{GS(th)} < 1.5 V$).
- Gate-Source Zener for ESD ruggedness (>6 kV Human Body Model).
- Compact industry standard SC70-6 surface mount package.



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	-25	V
V _{GSS}	Gate-Source Voltage	±8	V
I _D	Drain Current - Continuous (Note 1a) - Pulsed	-0.65 -1.8	A
P _D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	0.75 0.48	W
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf/1500 Ohm)	6.0	kV

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1b)	260	°C/W
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Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.14	FDG314P	7"	8mm	3000 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-25			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-19		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.65	-0.72	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -0.5\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -0.5\text{ A}$ @ 125°C $V_{GS} = -2.7\text{ V}, I_D = -0.25\text{ A}$		0.77 1.08 1.06	1.1 1.8 1.5	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-1			A
g_{FS}	Forward Transconductance	$V_{DS} = -4.5\text{ V}, I_D = -0.5\text{ A}$		0.9		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		63		pF
C_{oss}	Output Capacitance			34		pF
C_{rss}	Reverse Transfer Capacitance			10		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -6\text{ V}, I_D = -0.5\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 50\ \Omega$		7	20	ns
t_r	Turn-On Rise Time			8	20	ns
$t_{d(off)}$	Turn-Off Delay Time			55	110	ns
t_f	Turn-Off Fall Time			35	70	ns
Q_g	Total Gate Charge	$V_{DS} = -5\text{ V}, I_D = -0.25\text{ A},$ $V_{GS} = -4.5\text{ V}$		1.1	1.5	nC
Q_{gs}	Gate-Source Charge			0.32		nC
Q_{gd}	Gate-Drain Charge			0.25		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				-0.42	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.42\text{ A}$ (Note 2)		-0.85	-1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
 - 170 $^\circ\text{C/W}$ when mounted on a 1 in² pad of 2oz copper.
 - 260 $^\circ\text{C/W}$ when mounted on a minimum mounting pad.
- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

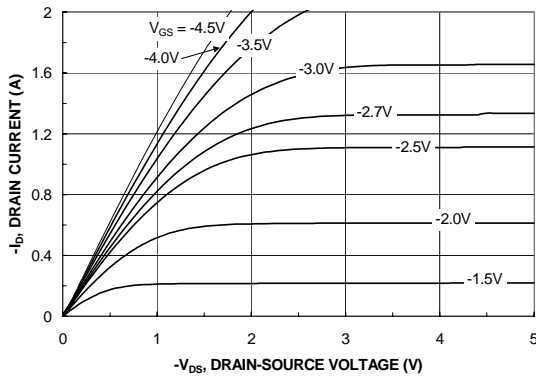


Figure 1. On-Region Characteristics.

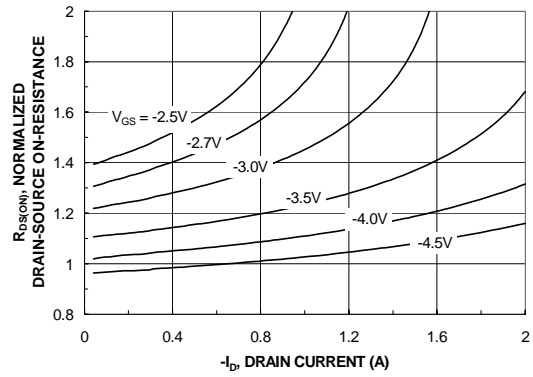


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

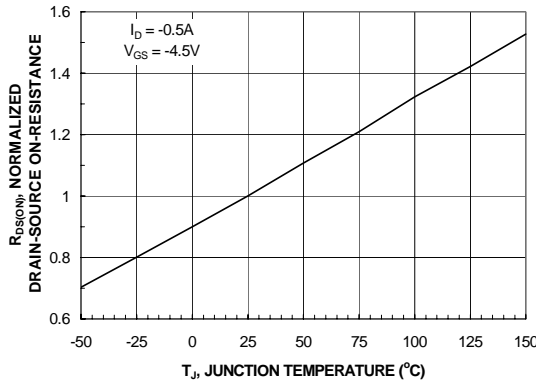


Figure 3. On-Resistance Variation with Temperature.

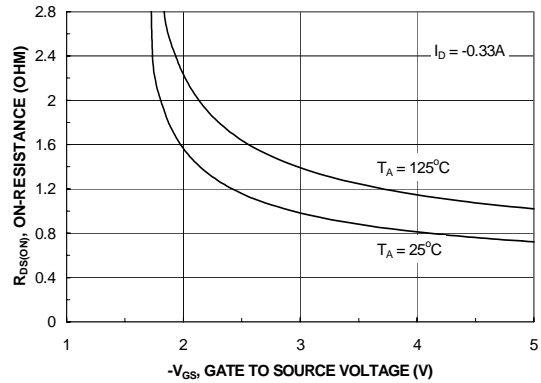


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

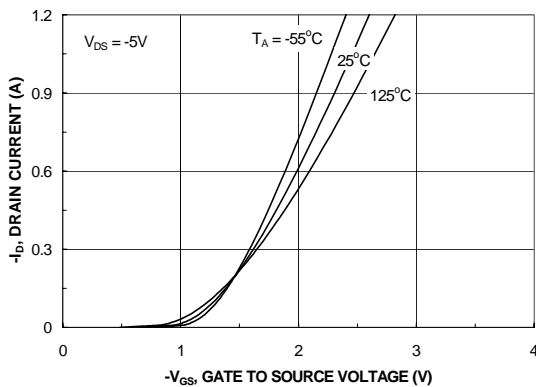


Figure 5. Transfer Characteristics.

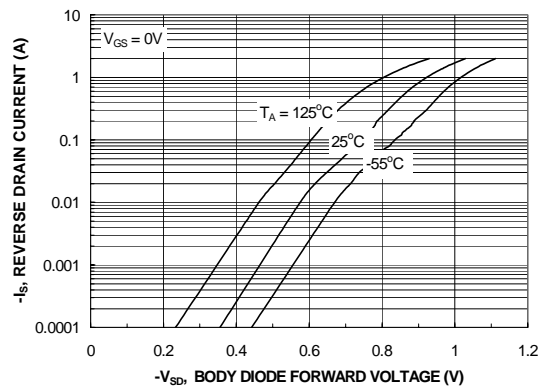


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

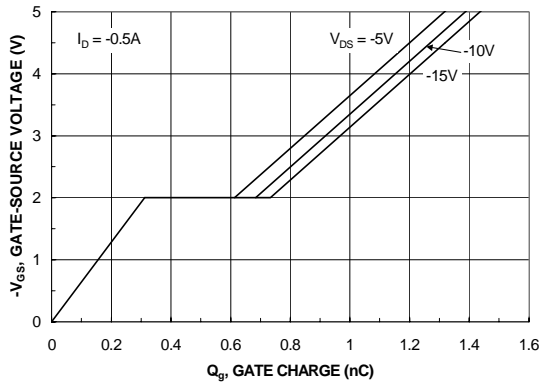


Figure 7. Gate-Charge Characteristics.

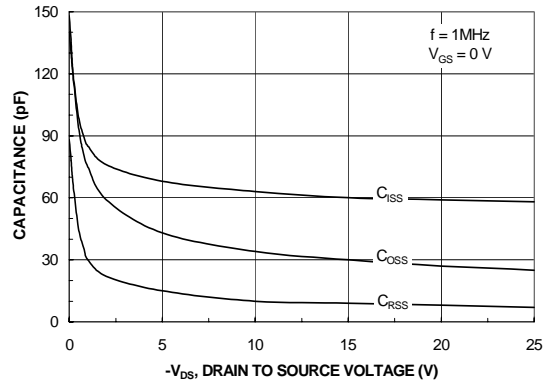


Figure 8. Capacitance Characteristics.

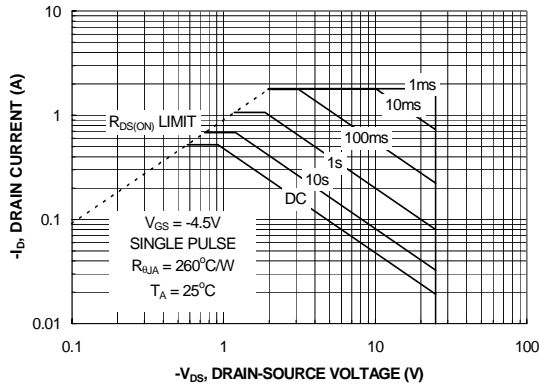


Figure 9. Maximum Safe Operating Area.

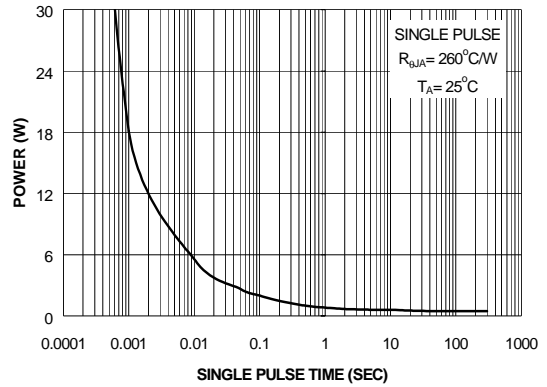


Figure 10. Single Pulse Maximum Power Dissipation.

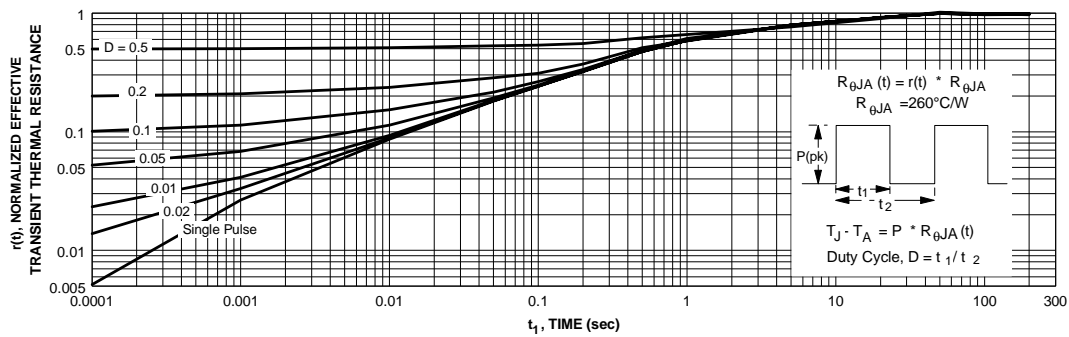


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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